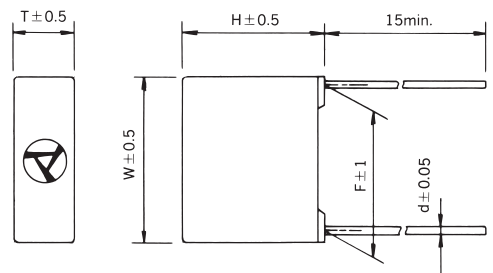


Features

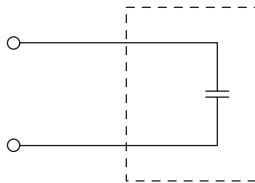
- Resin-mode case, Small in size
- Improved safty and suppressed self-heating

Application

- High frequency circuit, High voltage resonant circuit , Snubber circuit
- Protection of semiconductors such as IGBT, IPM and MOSFET.



Circuit diagram

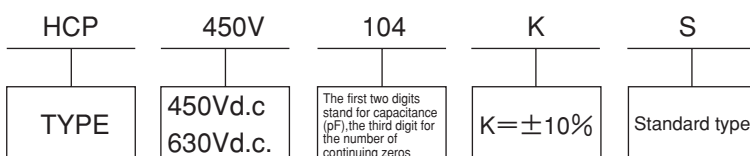


Unit : mm

Capacitance PART NO.	Rated voltage μF	450VDC					630VDC					Dissipation factor	Test voltage	Insulation resistance
		W	T	H	F	d	W	T	H	F	d			
103	0.01						17.5	5.0	12.0	15.0	0.6	0.001max (f=1000 ±100Hz)	Rated voltage ×1.75 (2~5sec)	50000MΩ min (at 20°C 100VDC)
153	0.015						∕	∕	∕	∕	∕			
223	0.022						∕	∕	∕	∕	∕			
333	0.033						∕	∕	∕	∕	∕			
473	0.047	17.0	5.0	12.0	15.0	0.6	∕	5.5	12.5	∕	0.8			
683	0.068	∕	5.5	12.5	∕	0.8	∕	6.5	13.5	∕	∕			
104	0.1	∕	6.5	13.5	∕	∕	∕	8.0	15.0	∕	∕			
154	0.15	∕	8.0	15.0	∕	∕	25.0	∕	17.5	22.5	∕			
224	0.22	25.0	6.5	16.0	22.5	∕	∕	∕	∕	∕	∕			
334	0.33	∕	8.0	17.5	∕	∕	∕	10.0	19.5	∕	∕			
474	0.47	30.0	11.0	22.0	27.5	∕	30.0	11.0	22.0	27.5	∕			
684	0.68	∕	∕	∕	∕	∕	∕	13.5	24.5	∕	∕			
105	1.0	∕	13.5	24.5	∕	∕	30.5	16.0	28.0	∕	1.0			
155	1.5						41.0	15.5	∕	37.5	∕			
225	2.2						∕	17.5	32.5	∕	∕			

Operating temperature : -40~+85°C

● Model coding system



Features

- Resine-mode case, Small in size
- Improved safty and suppressed self-heating

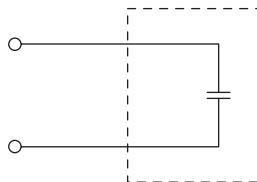
Application

- High frequency circuit, High voltage resonant circuit , Snubber circuit
- Protection of semiconductors such as IGBT, IPM and MOSFET.



Unit : mm

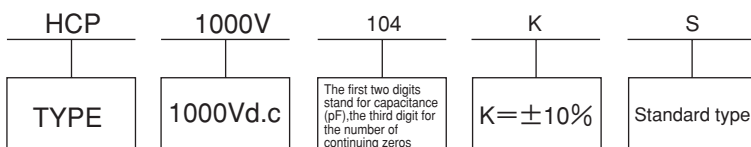
Circuit diagram



Capacitance PART NO.	Rated voltage μ F	1000VDC					Dissipation factor (f=1000 ±100Hz)	Test voltage Rated voltage × 1.75 (2~5sec)	Insulation resistance 50000MΩ min 20000Ω Fmin (at 20°C 100Vdc)
		W	T	H	F	d			
104	0.1	25.0	8.0	17.5	22.5	0.8			
474	0.47	30.5	16.0	28.0	27.5	1.0			
105	1.0	41.0	17.5	32.5	37.5	1.0			

Operating temperature -40°C ~ +85°C

● Model coding system

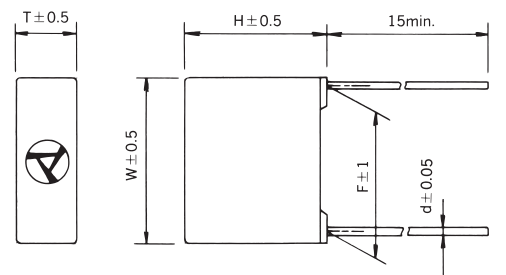


Features

- Resine-mode cace, Small in size
- Improved safty and suppressed self-hearing

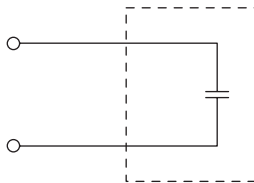
Application

- High frequency circuit, High voltage resonant circuit , Snubber circuit
- Protection of semiconductors such as IGBT, IPM and MOSFET.



Unit : mm

Circuit diagram



Capacitance PART NO.	Rated voltage μF	1250Vdc					Dissipation factor	Test voltage	Insulation resistance
		W	T	H	F	d			
103	0.01	17.0	8.0	15.0	15.0	0.8	Rated voltage ×1.75 (2~5sec)	50000MΩ min (at 20°C 100Vdc)	
153	0.015	25.0	6.5	16.0	22.5	∕			
223	0.022	∕	∕	∕	∕	∕			
333	0.033	∕	8.0	17.5	∕	∕			
473	0.047	∕	10.0	19.5	∕	∕			
683	0.068	30.0	11.0	22.0	27.5	∕			
104	0.1	∕	13.5	24.5	∕	∕			
154	0.15	30.5	16.0	28.0	∕	1.0			
224	0.22	41.0	15.5	∕	37.5	∕			
334	0.33	∕	∕	∕	∕	∕			
474	0.47	∕	17.5	32.5	∕	∕	20000Ω Fmin		

Operating temperature : -40~+85°C

● Model coding system

